

MULTI-CHIP TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM} : 300\text{mW (Tamb}=25^{\circ}\text{C)}$$

Collector current

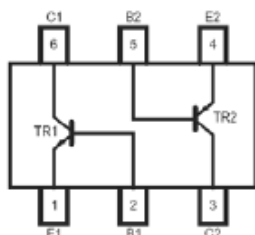
$$I_{CM} : -200\text{mA}$$

Collector-base Voltage

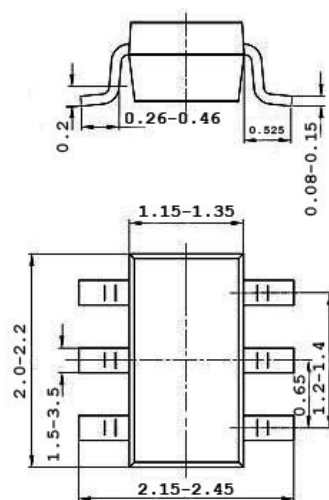
$$V_{(BR)CBO} : -50\text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



MARKING: 3C

SOT-363


UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-45			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
DC Current Gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	125		630	
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-0.3	V
	$V_{CE(sat)(2)}$	$I_C=-100\text{mA}, I_B=-5\text{mA}$			-0.65	V
Base-Emitter Voltage	$V_{BE(1)}$	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	-0.6		-0.75	V
	$V_{BE(2)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$			-0.82	V
Transition Frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$		200		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		3.5		pF
Noise Figure	NF	$V_{CE}=-5\text{V}, I_C=-0.2\text{mA}, f=1\text{KHz}, R_s=2\text{K}\Omega, BW=200\text{Hz}$		2.5		dB